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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Nobuaki MITAMURA et al.			
				FILING DATE December 21, 2005		GROUP <i>1702</i>	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
<i>F.H.</i>	1	JP A 11-147786 w/ abst & transl	6/2/1999	JAPAN			
<i>F.H.</i>	2	JP A 2000-178099 w/ abst & transl	6/27/2000	JAPAN			
<i>F.H.</i>	3	JP A 2002-201093 w/ abst & transl	7/16/2002	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>F.H.</i>	4	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643 {1982}					
<i>F.H.</i>	5	DUPRET et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No. 9, pp. 1849-1871 {1990}					
EXAMINER					DATE CONSIDERED		
Examiner:							
Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 21, 2005